

EPIGAP Optronic GmbH

Koepenicker Str. 325b
D-12555 Berlin
Fon: +49 (0)30 657637 60
Fax: +49 (0)30 657637 70
sales@epigap-optronic.de



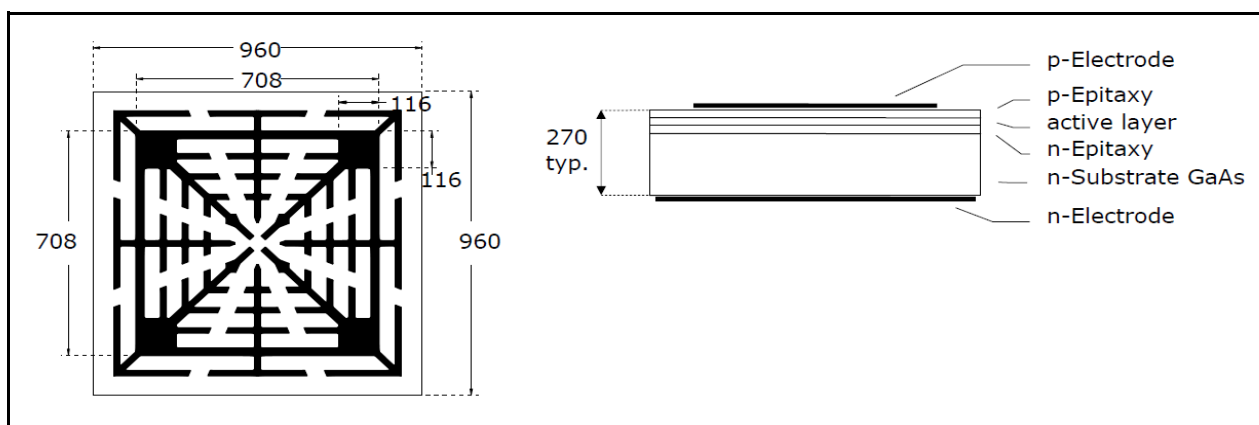
Data Sheet

LED Chip Infrared

EOLC-1020-11

Rev. 02, 2014

Radiation	Type	Electrodes
Infrared	GaAs	P (anode) up



Optical and Electrical Characteristics

T_{amb} = 25°C, unless otherwise specified

Parameter	Test cond.	Symbol	Min	Typ	Max	Unit
Forward voltage	I _F =100 mA	V _F		1.15	1.25	V
Forward voltage	I _F =350 mA	V _F		1.2	1.4	V
Reverse current	I _R =5 V	I _R			10	µA
Output power	I _F =50 mA	Φ _e		5		mW
Radiant intensity	I _F =350 mA	I _e		8.5		mW/sr
Peak wavelength	I _F =350 mA	λ _p	1000	1020	1040	nm
FWHM	I _F =350 mA	Δλ _{0.5}		40		nm
Switching time	I _F =350 mA	t _r , t _f		20		ns

¹ Measured on on gold plate

Labeling

Type	Lot N°	Φ _e (typ) [mW]	V _F (typ) [V]	Quantity
EOLC-1020-11				

Packing

Chips on adhesive film with wire-bond side top



We reserve the right to make changes to improve technical design and may do so without further notice. Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer.